Vishay General Semiconductor

# Dual High-Voltage TMBS® (Trench MOS Barrier Schottky) Rectifier

Ultra Low  $V_F = 0.36$  V at  $I_F = 5$  A



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## Anode 1 O K Anode 2 O Cathode

## LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS				
I <sub>F(AV)</sub>	2 x 30 A			
V <sub>RRM</sub>	100 V			
I <sub>FSM</sub>	320 A			
$V_F$ at $I_F$ = 30 A ( $T_A$ = 125 °C)	0.66 V			
T <sub>J</sub> max.	150 °C			
Package	SMPD (TO-263AC)			
Circuit configuration	Common cathode			

### FEATURES

- Trench MOS Schottky technology
- Very low profile typical height of 1.7 mm
- Ideal for automated placement
- Low forward voltage drop, low power losses
- High efficiency operation
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified available:
   Automotive ordering code: base P/NHM3
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

### **TYPICAL APPLICATIONS**

For use in high frequency DC/DC converters, switching power supplies, freewheeling diodes, OR-ing diode, and reverse battery protection in commercial, industrial, and automotive application.

### **MECHANICAL DATA**

Case: SMPD (TO-263AC)

Molding compound meets UL 94 V-0 flammability rating Base P/N-M3 - halogen-free, RoHS-compliant

Base P/NHM3 - halogen-free, RoHS-compliant, and AEC-Q101 qualified

**Terminals:** matte tin plated leads, solderable per J-STD-002 and JESD 22-B102

M3 and HM3 suffix meets JESD 201 class 2 whisker test **Polarity:** as marked

<b>MAXIMUM RATINGS</b> (T <sub>A</sub> = 25 °C unless otherwise noted)					
PARAMETER		SYMBOL	V60D100C	UNIT	
Maximum repetitive peak reverse voltage		V <sub>RRM</sub>	100	V	
Maximum average forward rectified current (fig. 1)	per device		60	٨	
	per diode	IF(AV)	30	A	
Peak forward surge current 10 ms single half sine-wave superimposed on rated load		I <sub>FSM</sub>	320	А	
Voltage rate of change (rated V <sub>R</sub> )		dV/dt	10 000	V/µs	
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>STG</sub>	-40 to +150	°C	





RoHS COMPLIANT HALOGEN

V60D100C



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<b>ELECTRICAL CHARACTERISTICS</b> ( $T_A = 25 \text{ °C}$ unless otherwise noted)							
PARAMETER	TEST CONDITIONS		SYMBOL	TYP.	MAX.	UNIT	
Instantaneous forward voltage per diode	I <sub>F</sub> = 5 A	T <sub>A</sub> = 25 °C	V <sub>F</sub> (1)	0.45	-	V	
	I <sub>F</sub> = 15 A			0.62	-		
	I <sub>F</sub> = 30 A			0.75	0.81		
	I <sub>F</sub> = 5 A	T <sub>A</sub> = 125 °C		0.36	-		
	I <sub>F</sub> = 15 A			0.54	-		
	I <sub>F</sub> = 30 A			0.66	0.73		
Reverse current at rated V <sub>R</sub> per diode	V <sub>R</sub> = 70 V	T <sub>A</sub> = 25 °C	I <sub>R</sub> <sup>(2)</sup>	12	-	μA	
		T <sub>A</sub> = 125 °C		11	-	mA	
	V <sub>R</sub> = 100 V	T <sub>A</sub> = 25 °C		-	1000	μA	
		T <sub>A</sub> = 125 °C		27	85	mA	

#### Notes

 $^{(1)}\,$  Pulse test: 300  $\mu s$  pulse width, 1  $\,\%$  duty cycle

<sup>(2)</sup> Pulse test: Pulse width  $\leq$  5 ms

<b>THERMAL CHARACTERISTICS</b> ( $T_A = 25$ °C unless otherwise noted)					
PARAMETER		SYMBOL	V60D100C	UNIT	
Typical thermal resistance	per diode	$R_{\theta JC}$	1.8	°C/W	
	per device	R <sub>θJC</sub>	0.95		
	per device	R <sub>0JM</sub> <sup>(2)</sup>	3		
	per device	R <sub>0JA</sub> <sup>(1)(2)</sup>	45		

Notes

<sup>(1)</sup> The heat generated must be less than the thermal conductivity from junction-to-ambient:  $dP_D/dT_J < 1/R_{\theta JA}$ 

<sup>(2)</sup> Free air, without heatsink; thermal resistance  $R_{\theta JA}$  - junction to ambient; thermal resistance  $R_{\theta JM}$  - junction to mount

ORDERING INFORMATION (Example)					
PACKAGE	PREFERRED P/N	UNIT WEIGHT (g)	PACKAGE CODE	BASE QUANTITY	DELIVERY MODE
SMPD (TO-263AC)	V60D100C-M3/I	0.55	I	2000/reel	13" diameter plastic tape and reel
SMPD (TO-263AC)	V60D100CHM3/I (1)	0.55	I	2000/reel	13" diameter plastic tape and reel

#### Note

(1) AEC-Q101 qualified



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## RATINGS AND CHARACTERISTICS CURVES (T<sub>A</sub> = 25 °C unless otherwise noted)

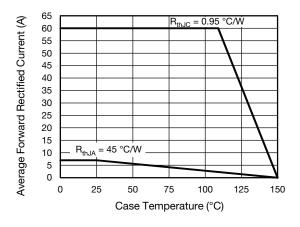


Fig. 1 - Forward Current Derating Curve

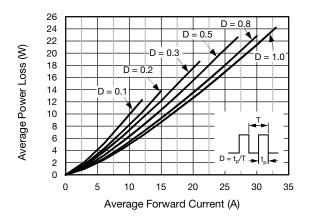


Fig. 2 - Forward Power Loss Characteristics Per Diode

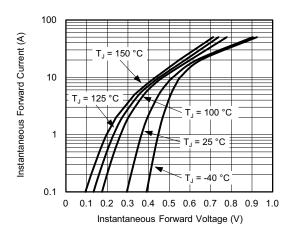


Fig. 3 - Typical Instantaneous Forward Characteristics Per Diode

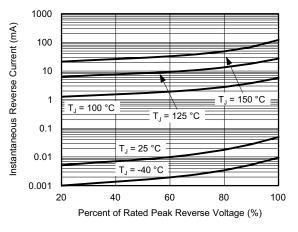


Fig. 4 - Typical Reverse Characteristics Per Diode

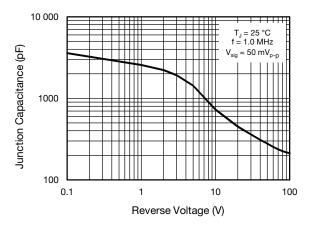


Fig. 5 - Typical Junction Capacitance Per Diode

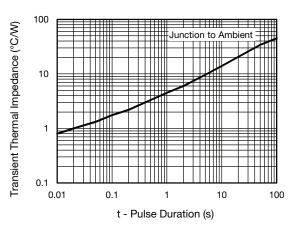


Fig. 6 - Typical Transient Thermal Impedance Per Device

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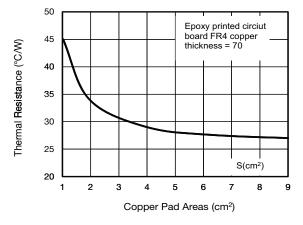
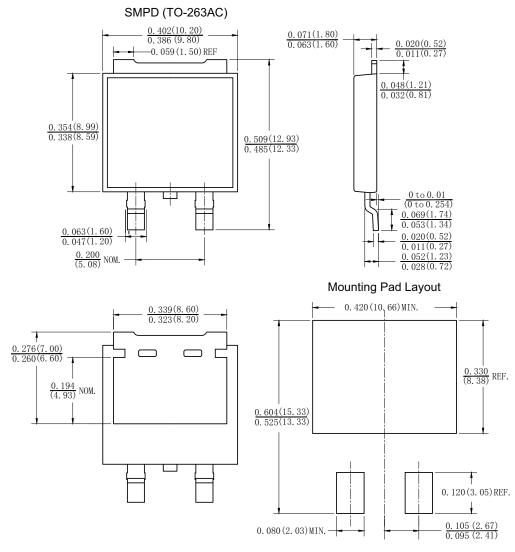


Fig. 7 - Thermal Resistance Junction-to-Ambient vs. Copper Pad Areas





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